

74AUP1G04

Low-power inverter

Rev. 7 — 27 June 2012

Product data sheet

1. General description

The 74AUP1G04 provides the single inverting buffer.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} .

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G04GV	−40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74AUP1G04GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G04GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G04GF	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AUP1G04GN	−40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1G04GS	−40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1G04GX	−40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.35 mm	SOT1226

4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G04GV	p04
74AUP1G04GW	pC
74AUP1G04GM	pC
74AUP1G04GF	pC
74AUP1G04GN	pC
74AUP1G04GS	pC
74AUP1G04GX	pC

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

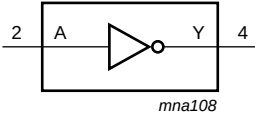


Fig 1. Logic symbol

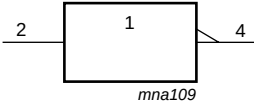


Fig 2. IEC logic symbol

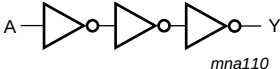
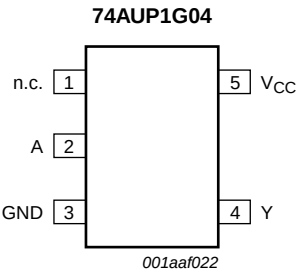


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning



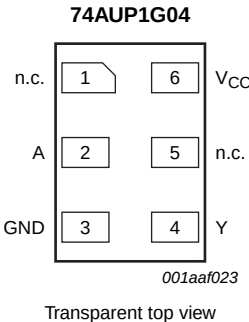
74AUP1G04

n.c. 1 5 V_{CC}

A 2

GND 3 4 Y

001aaf022



74AUP1G04

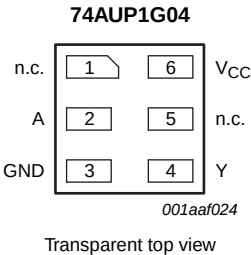
n.c. 1 6 V_{CC}

A 2 5 n.c.

GND 3 4 Y

001aaf023

Transparent top view



74AUP1G04

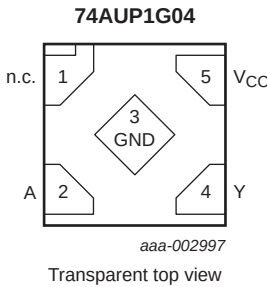
n.c. 1 6 V_{CC}

A 2 5 n.c.

GND 3 4 Y

001aaf024

Transparent top view



74AUP1G04

n.c. 1 5 V_{CC}

A 2 4 Y

3 GND

aaa-002997

Transparent top view

Fig 4. Pin configuration SOT353-1 and SOT753

Fig 5. Pin configuration SOT886

Fig 6. Pin configuration SOT891, SOT1115 and SOT1202

Fig 7. Pin configuration SOT1226 (X2SON5)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table^[1]

Input	Output
A	Y
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		^[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage	active mode	^[1] -0.5	$V_{CC} + 0.5$	V
		power-down mode	^[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	+50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	active mode	0	V_{CC}	V
		power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	40	µA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.8	-	pF
C _O	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.7	-	pF

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.5	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	50	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	75	µA

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = 25 °C; C_L = 5 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 ^[2]				
		V _{CC} = 0.8 V	-	16.0	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	5.0	10.3	ns
		V _{CC} = 1.4 V to 1.6 V	1.8	3.6	6.4	ns
		V _{CC} = 1.65 V to 1.95 V	1.5	2.9	5.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.2	2.4	3.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.1	2.1	3.2	ns
T_{amb} = 25 °C; C_L = 10 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 ^[2]				
		V _{CC} = 0.8 V	-	19.8	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.8	5.9	12.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	4.2	7.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.5	5.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	2.9	4.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	2.7	3.8	ns
T_{amb} = 25 °C; C_L = 15 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 ^[2]				
		V _{CC} = 0.8 V	-	23.3	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	6.7	13.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.6	4.7	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.0	6.7	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.3	5.1	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	3.1	4.2	ns
T_{amb} = 25 °C; C_L = 30 pF						
t _{pd}	propagation delay	A to Y; see Figure 8 ^[2]				
		V _{CC} = 0.8 V	-	33.6	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.4	8.9	16.0	ns
		V _{CC} = 1.4 V to 1.6 V	3.6	6.3	10.8	ns
		V _{CC} = 1.65 V to 1.95 V	3.2	5.3	9.0	ns
		V _{CC} = 2.3 V to 2.7 V	2.9	4.5	6.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.9	4.2	5.4	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = 25 °C						
C _{PD}	power dissipation capacitance	f = 1 MHz; V _I = GND to V _{CC} ^[3]				
		V _{CC} = 0.8 V	-	2.5	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.7	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	2.8	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	3.0	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	3.5	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	4.0	-	pF

[1] All typical values are measured at nominal V_{CC}.[2] t_{pd} is the same as t_{PLH} and t_{PHL}.[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.**Table 9. Dynamic characteristics**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#)

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	

C_L = 5 pF

t _{pd}	propagation delay	A to Y; see Figure 8 ^[1]					
		V _{CC} = 1.1 V to 1.3 V	2.1	11.4	2.1	12.6	ns
		V _{CC} = 1.4 V to 1.6 V	1.6	7.4	1.6	8.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.4	5.9	1.4	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.1	4.5	1.1	5.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.9	1.0	4.3	ns

C_L = 10 pF

t _{pd}	propagation delay	A to Y; see Figure 8 ^[1]					
		V _{CC} = 1.1 V to 1.3 V	2.6	13.7	2.6	15.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	8.7	2.1	9.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.8	7.0	1.8	7.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	5.4	1.5	6.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	4.5	1.4	5.0	ns

Table 9. Dynamic characteristics ...continued
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions	−40 °C to +85 °C		−40 °C to +125 °C		Unit	
			Min	Max	Min	Max		
C _L = 15 pF								
t _{pd}	propagation delay	A to Y; see Figure 8	[1]					
		V _{CC} = 1.1 V to 1.3 V		3.0	15.8	3.0	17.4	ns
		V _{CC} = 1.4 V to 1.6 V		2.4	10.0	2.4	11.0	ns
		V _{CC} = 1.65 V to 1.95 V		2.1	8.0	2.1	8.8	ns
		V _{CC} = 2.3 V to 2.7 V		1.8	6.1	1.8	6.8	ns
		V _{CC} = 3.0 V to 3.6 V		1.8	5.0	1.8	5.5	ns
C _L = 30 pF								
t _{pd}	propagation delay	A to Y; see Figure 8	[1]					
		V _{CC} = 1.1 V to 1.3 V		4.0	19.0	4.0	20.9	ns
		V _{CC} = 1.4 V to 1.6 V		3.2	12.9	3.2	14.2	ns
		V _{CC} = 1.65 V to 1.95 V		2.9	10.5	2.9	11.6	ns
		V _{CC} = 2.3 V to 2.7 V		2.6	7.6	2.6	8.4	ns
		V _{CC} = 3.0 V to 3.6 V		2.6	6.2	2.6	6.9	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

12. Waveforms

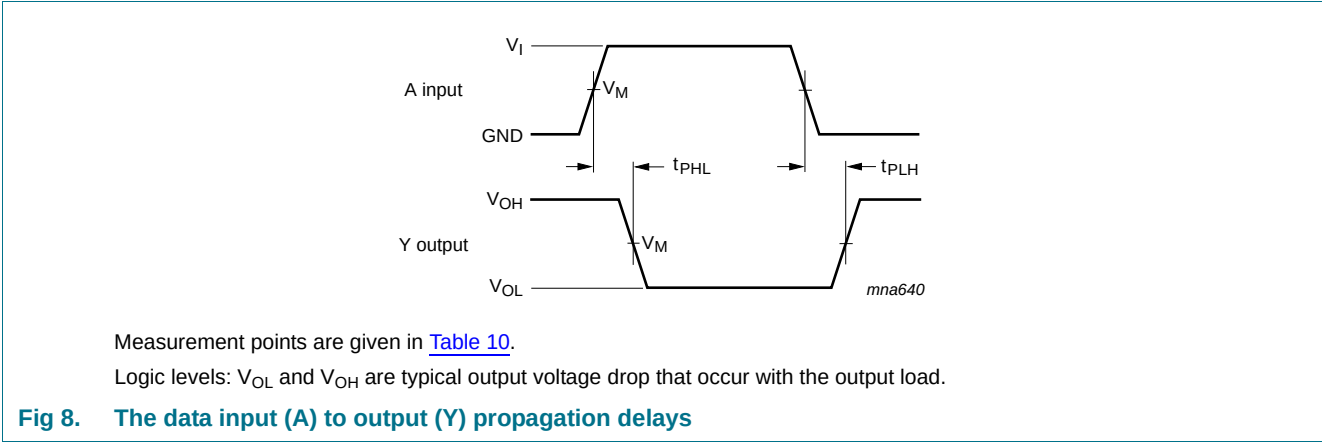
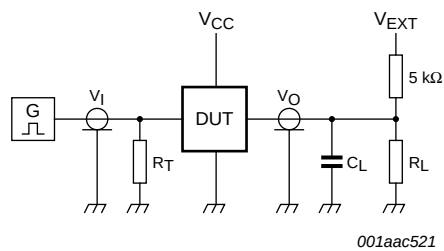


Table 10. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	V _I	t _r = t _f
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns



Test data is given in [Table 11](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance
 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator
 V_{EXT} = External voltage for measuring switching times.

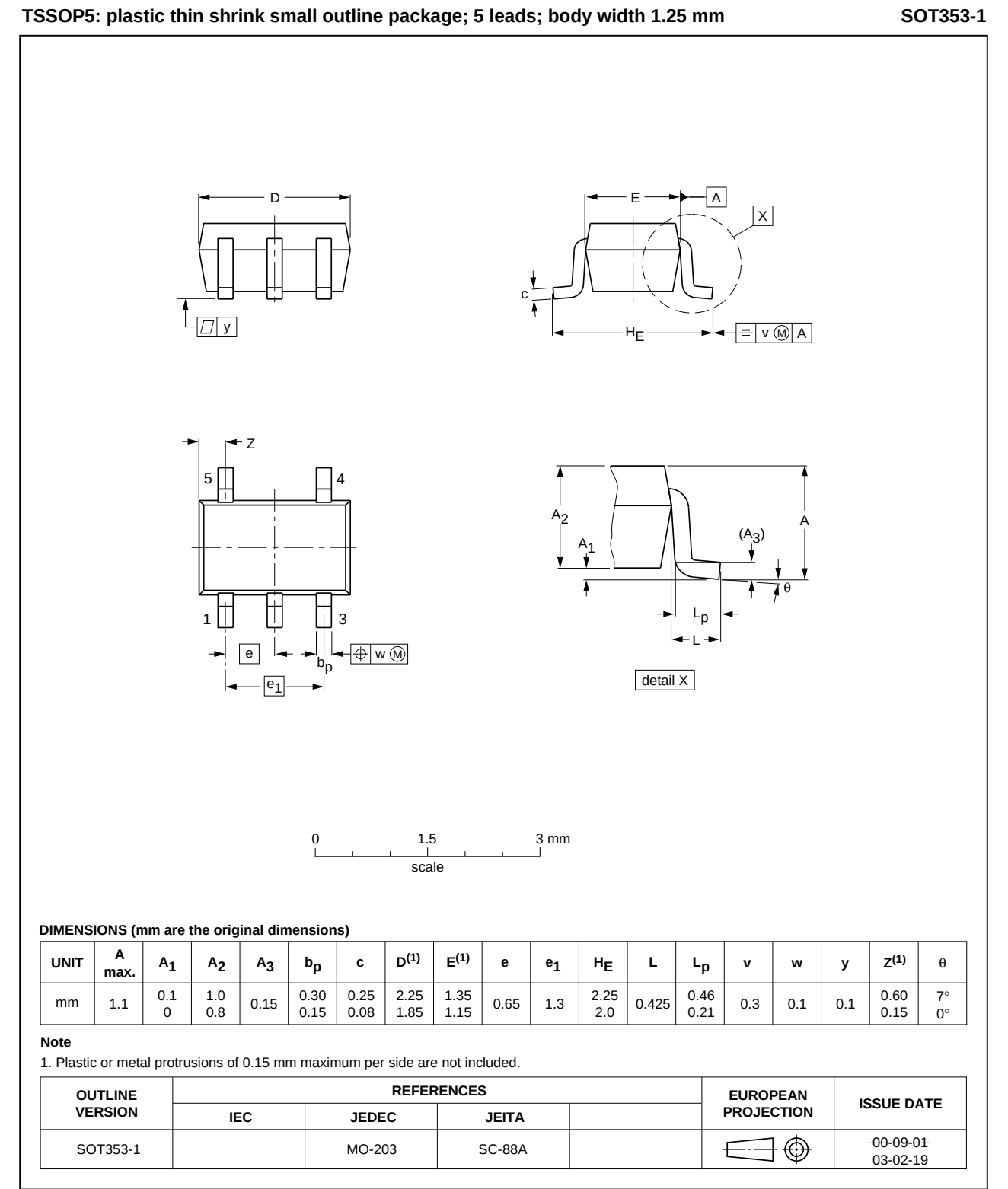
Fig 9. Load circuitry for switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH} , t_{PHL}	t_{PZH} , t_{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5\text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1\text{ M}\Omega$.

13. Package outline



Plastic surface-mounted package; 5 leads

SOT753

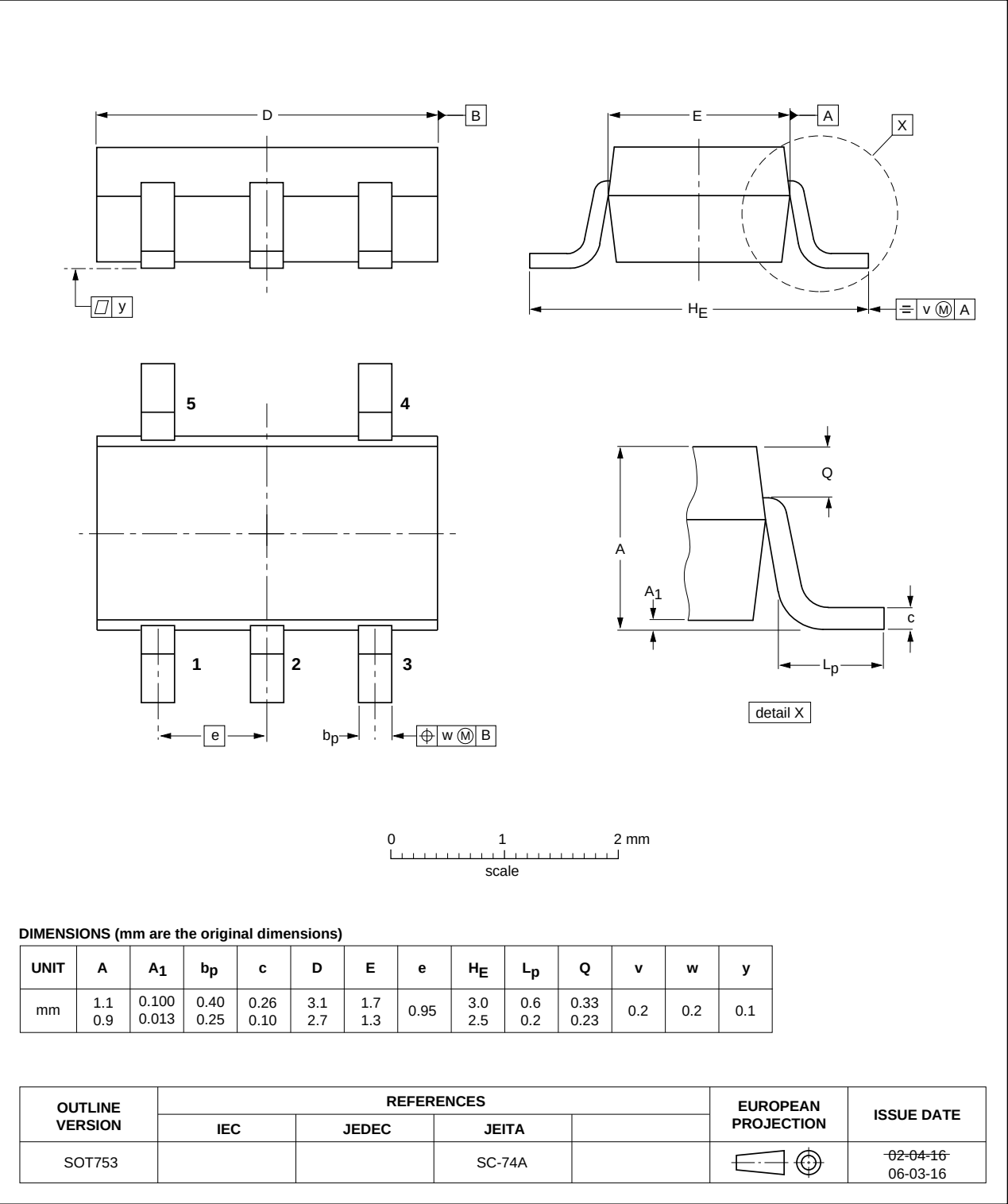


Fig 11. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

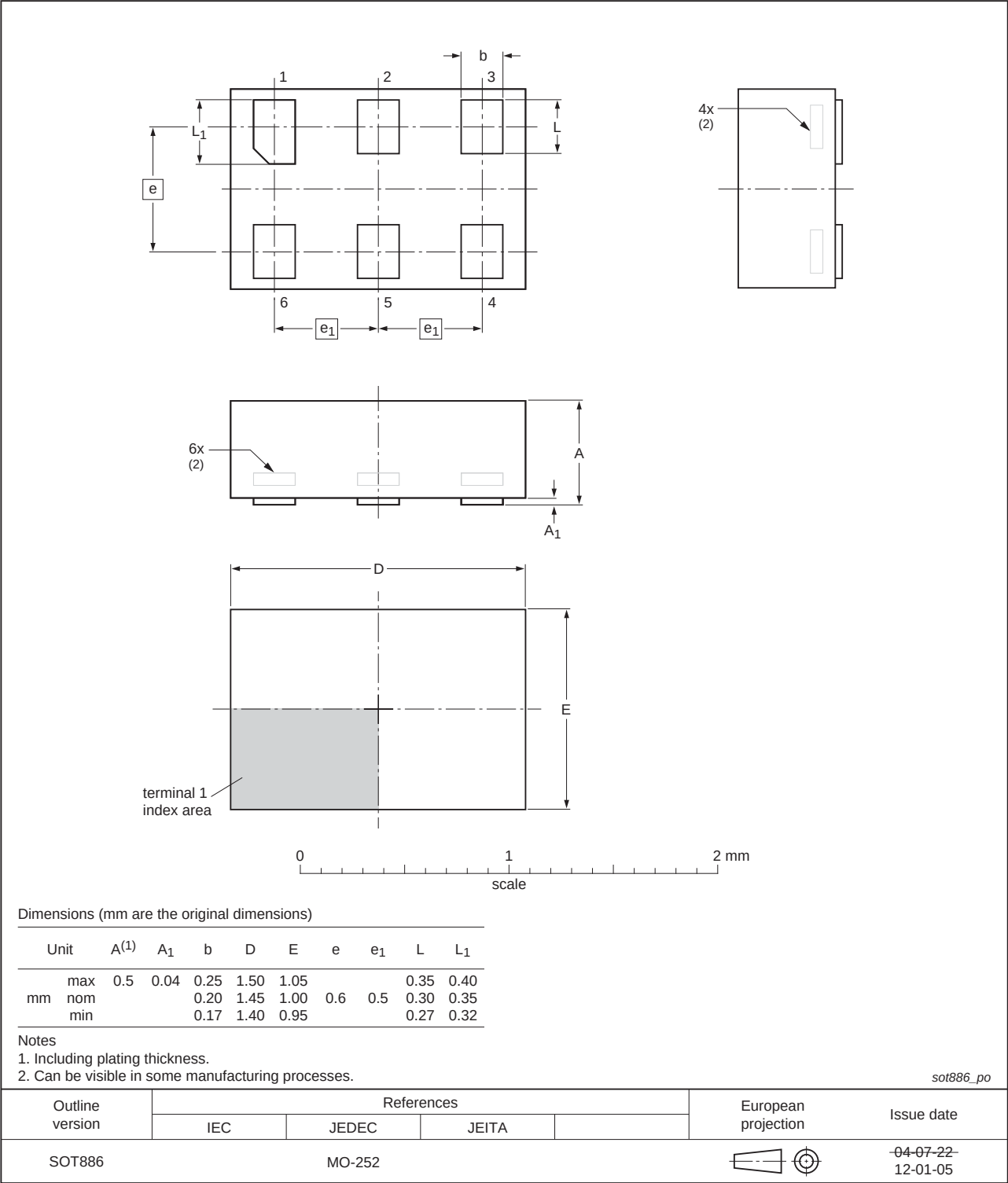


Fig 12. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

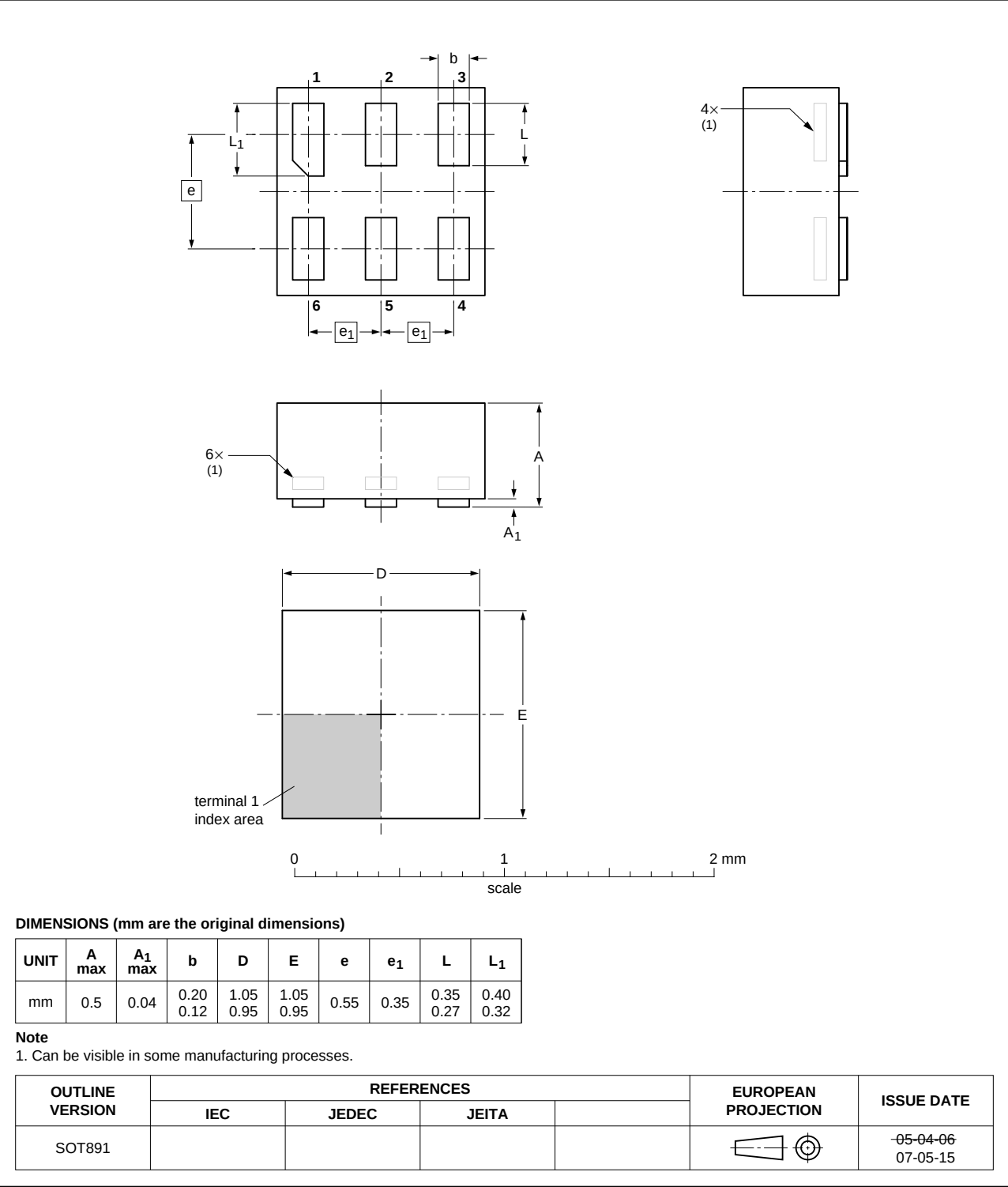


Fig 13. Package outline SOT891 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm

SOT1115

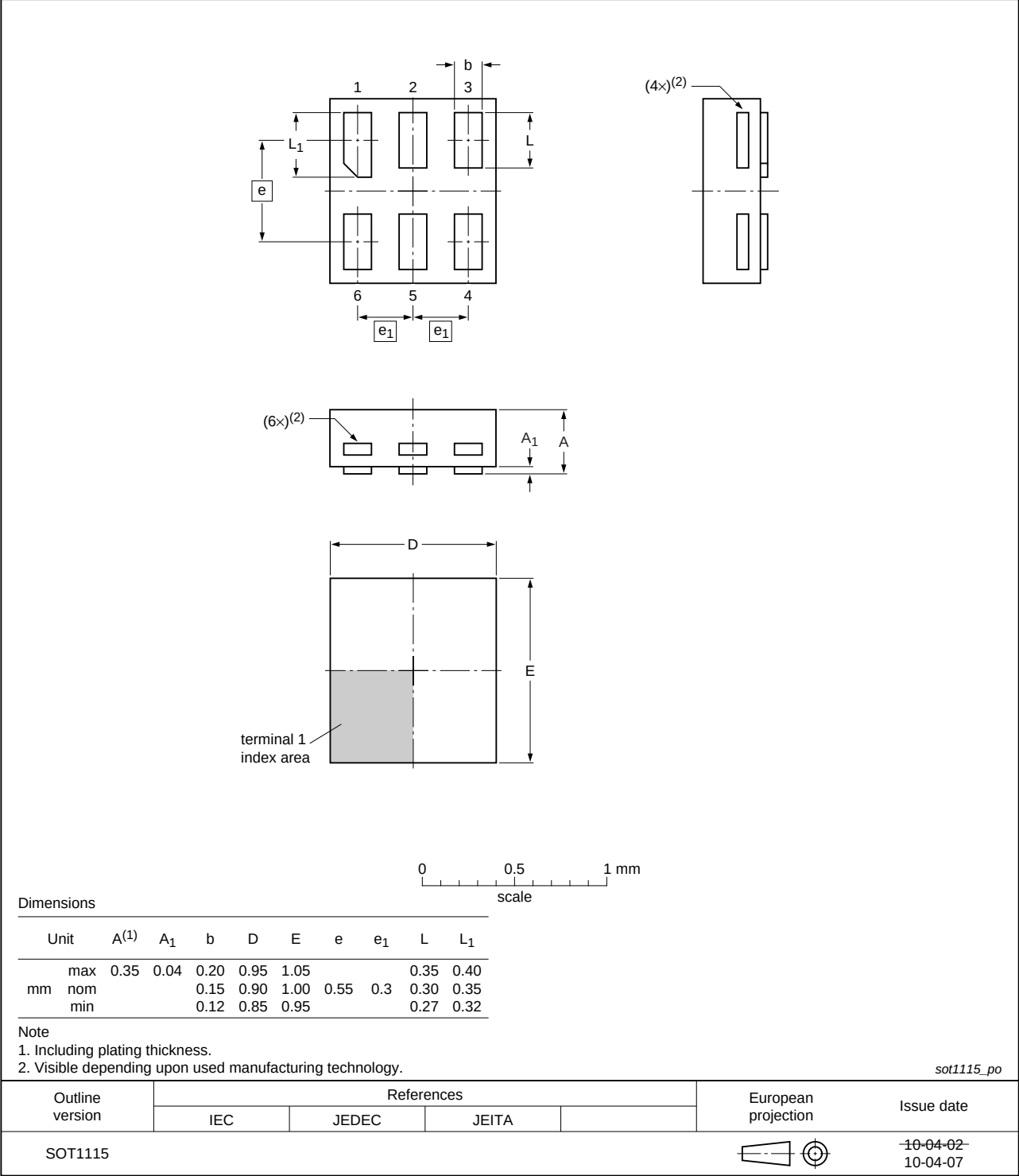


Fig 14. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm

SOT1202

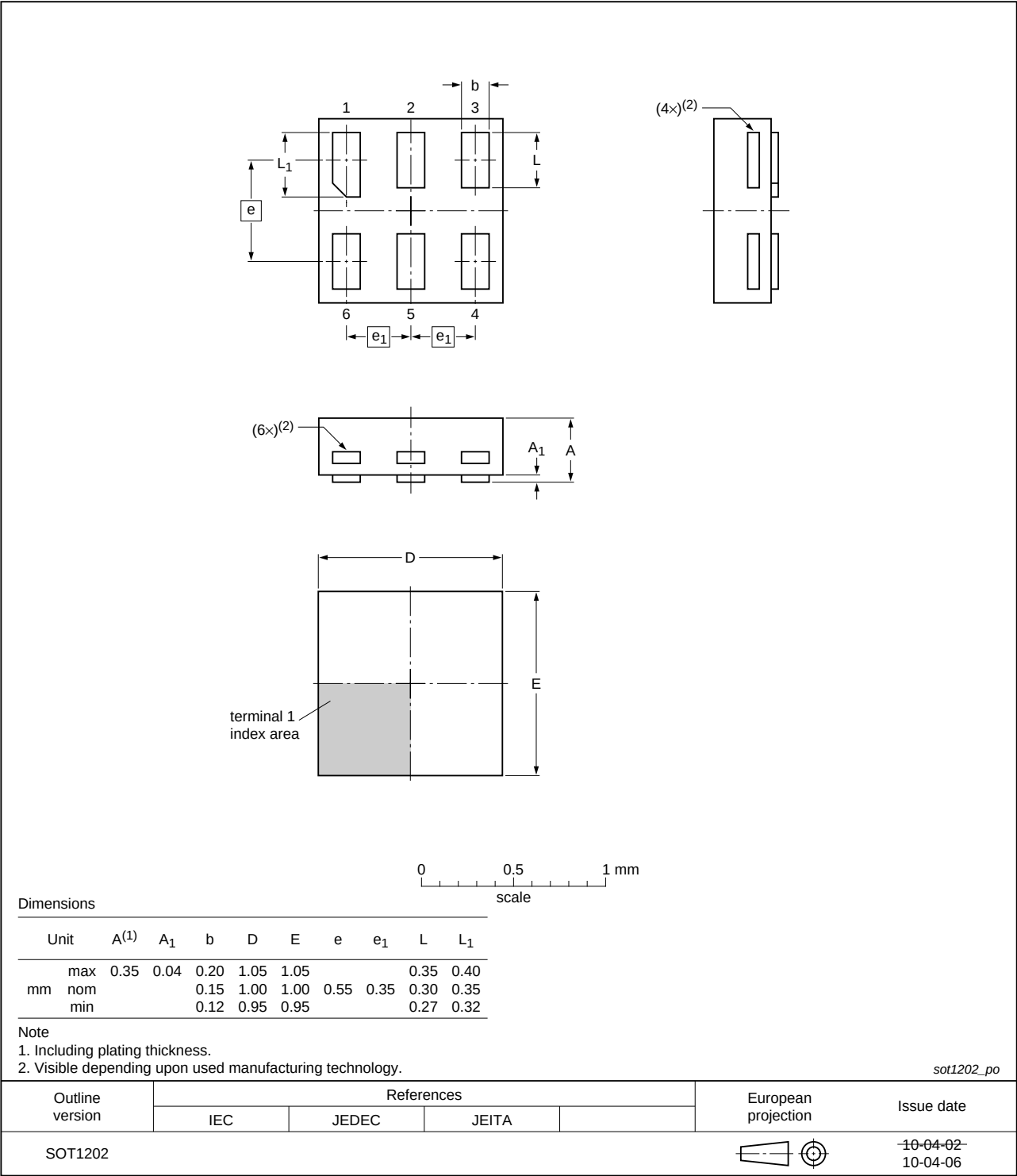


Fig 15. Package outline SOT1202 (XSON6)

X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;
5 terminals; body 0.8 x 0.8 x 0.35 mm

SOT1226

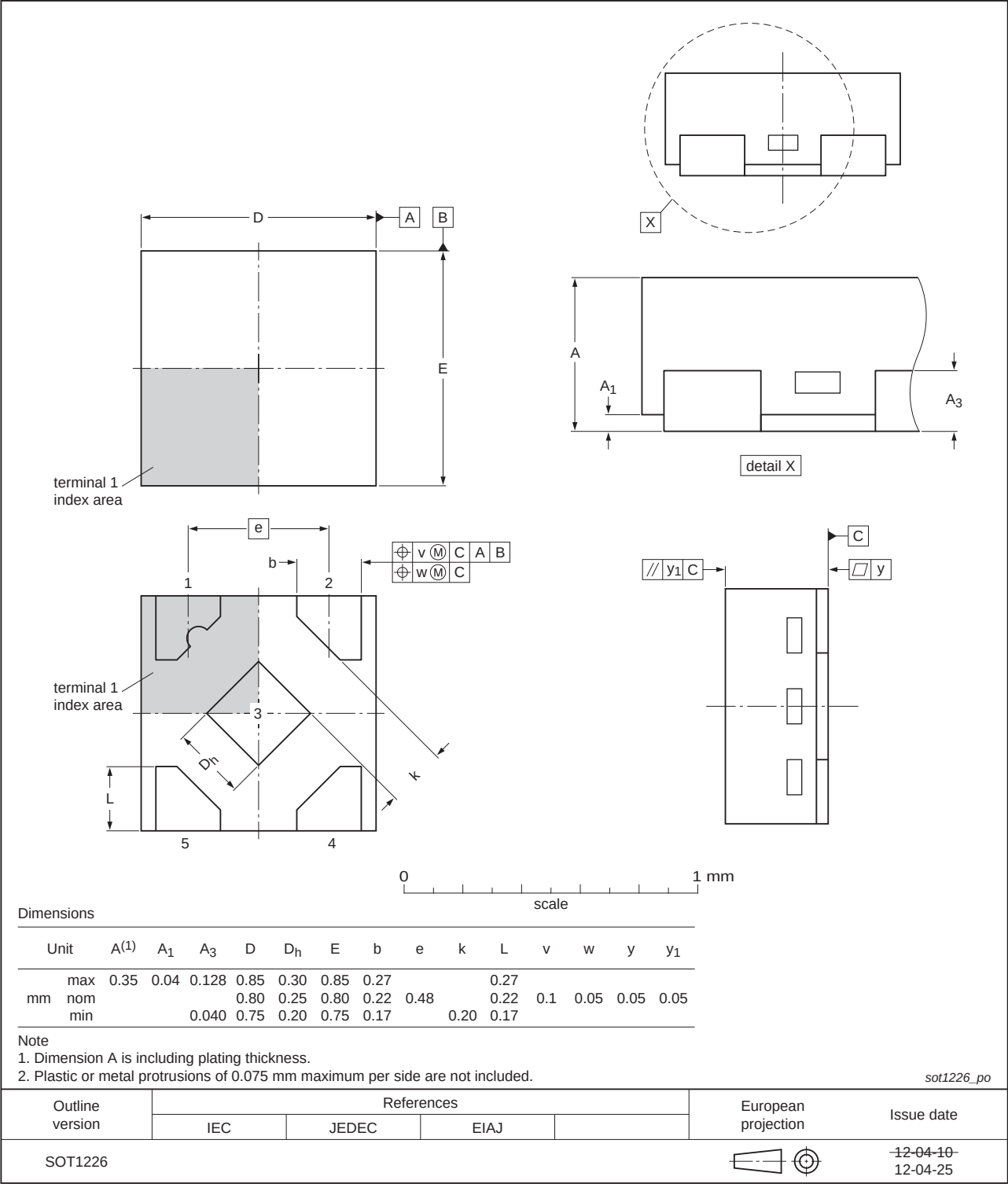


Fig 16. Package outline SOT1226 (X2SON5)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G04 v.7	20120627	Product data sheet	-	74AUP1G04 v.6
Modifications:	• Added type number 74AUP1G04GX (SOT1226)			
74AUP1G04 v.6	20120214	Product data sheet	-	74AUP1G04 v.5
Modifications:	• Package outline drawing of SOT886 (Figure 12) modified.			
74AUP1G04 v.5	20111205	Product data sheet	-	74AUP1G04 v.4
Modifications:	• Legal pages updated.			
74AUP1G04 v.4	20100630	Product data sheet	-	74AUP1G04 v.3
74AUP1G04 v.3	20091105	Product data sheet	-	74AUP1G04 v.2
74AUP1G04 v.2	20060628	Product data sheet	-	74AUP1G04 v.1
74AUP1G04 v.1	20050718	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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